



EE 232 Lightwave Devices

Lecture 9: Optical Matrix Element, k-Selection Rule, Quantum Well Gain / Absorption

Instructor: Ming C. Wu

**University of California, Berkeley
Electrical Engineering and Computer Sciences Dept.**

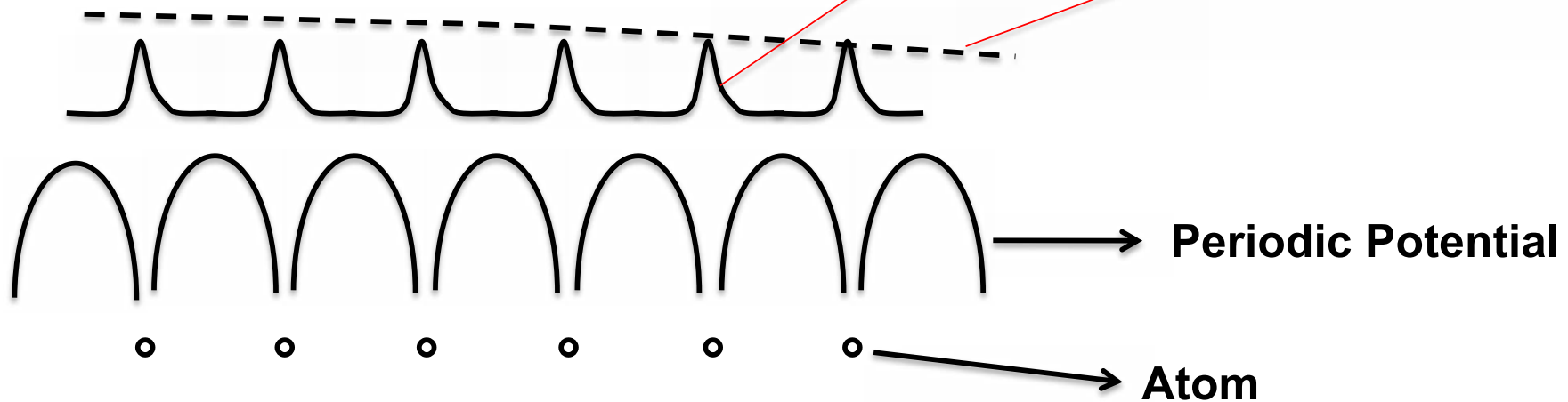


Bloch Function

- Bloch function
 - Electron wavefunction in a periodic potential can be expressed as a product of a periodic function and a slowly varying plane wave envelop function

$$|a\rangle = \psi_a(\vec{r}) = u_v(\vec{r}) \frac{e^{i\vec{k}_v \cdot \vec{r}}}{\sqrt{V}}$$

$$|b\rangle = \psi_b(\vec{r}) = u_c(\vec{r}) \frac{e^{i\vec{k}_c \cdot \vec{r}}}{\sqrt{V}}$$





Optical Matrix Element

$$H'_{ba} = \langle b | \left(-\frac{eA_0}{2m_0} \hat{e} \cdot \vec{P} \right) | a \rangle = -\frac{eA_0}{2m_0} \hat{e} \cdot \langle b | \vec{P} | a \rangle = -\frac{eA_0}{2m_0} \hat{e} \cdot \vec{P}_{ba}$$

Electron wavefunction can be expressed in Bloch functions:

$$|a\rangle = \psi_a(\vec{r}) = u_v(\vec{r}) \frac{e^{i\vec{k}_v \cdot \vec{r}}}{\sqrt{V}}; \quad |b\rangle = \psi_b(\vec{r}) = u_c(\vec{r}) \frac{e^{i\vec{k}_c \cdot \vec{r}}}{\sqrt{V}}$$

$$H'_{ba} = -\frac{eA_0}{2m_0} \hat{e} \cdot \langle b | \vec{P} | a \rangle = -\frac{eA_0}{2m_0} \hat{e} \cdot \int u_c^*(\vec{r}) e^{-i\vec{k}_c \cdot \vec{r}} e^{i\vec{k}_{op} \cdot \vec{r}} (-i\hbar \nabla) u_v(\vec{r}) e^{i\vec{k}_v \cdot \vec{r}} \frac{d^3 r}{V}$$

$$= -\frac{eA_0}{2m_0} \hat{e} \cdot \int u_c^*(\vec{r}) e^{-i\vec{k}_c \cdot \vec{r}} e^{i\vec{k}_{op} \cdot \vec{r}} \left[(-i\hbar \nabla) u_v(\vec{r}) + (-i\hbar \vec{k}_v) u_v(\vec{r}) \right] e^{i\vec{k}_v \cdot \vec{r}} \frac{d^3 r}{V}$$

$$= -\frac{eA_0}{2m_0} \hat{e} \cdot \int u_c^*(\vec{r}) (-i\hbar \nabla) u_v(\vec{r}) \frac{d^3 r}{\Omega} \int e^{-i\vec{k}_c \cdot \vec{r}} e^{i\vec{k}_{op} \cdot \vec{r}} e^{i\vec{k}_v \cdot \vec{r}} \frac{d^3 r}{V}$$

Slowly Varying Envelop Approx

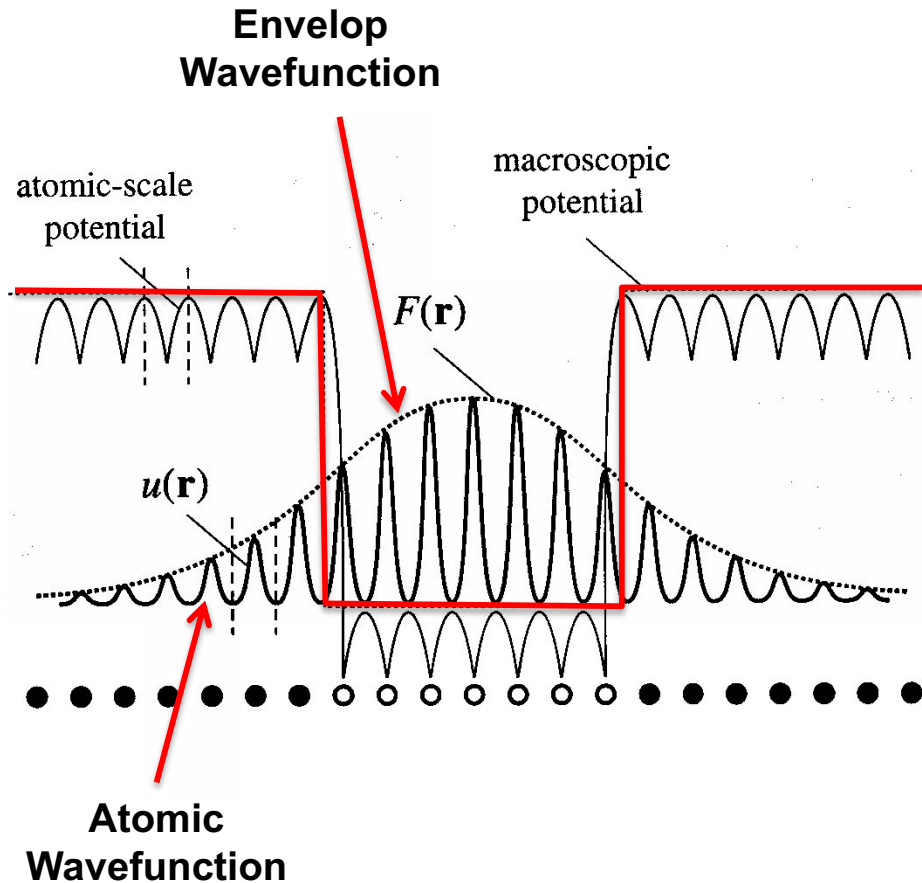
$$= -\frac{eA_0}{2m_0} \hat{e} \cdot \vec{p}_{cv} \cdot \delta_{\vec{k}_c, \vec{k}_{op} + \vec{k}_v} \rightarrow \text{k-Selection Rule}$$

Matrix element of periodic function over unit cell



Optical Matrix Element for Quantum Wells

Quantum Well Wavefunction



$$|a\rangle = \psi_a(\vec{r}) = u_v(\vec{r}) \frac{e^{i\vec{k}_t \cdot \vec{\rho}}}{\sqrt{A}} g_m(z)$$

$$|b\rangle = \psi_b(\vec{r}) = u_c(\vec{r}) \frac{e^{i\vec{k}_t \cdot \vec{\rho}}}{\sqrt{A}} \phi_n(z)$$

$$H'_{ba} = -\frac{eA_0}{2m_0} \hat{e} \cdot \langle b | \vec{P} | a \rangle$$

$$= -\frac{eA_0}{2m_0} \hat{e} \cdot \vec{p}_{cv} \cdot \delta_{\vec{k}_t, \vec{k}_t'} \cdot I_{hm}^{en}$$

Slowly Varying Envelop

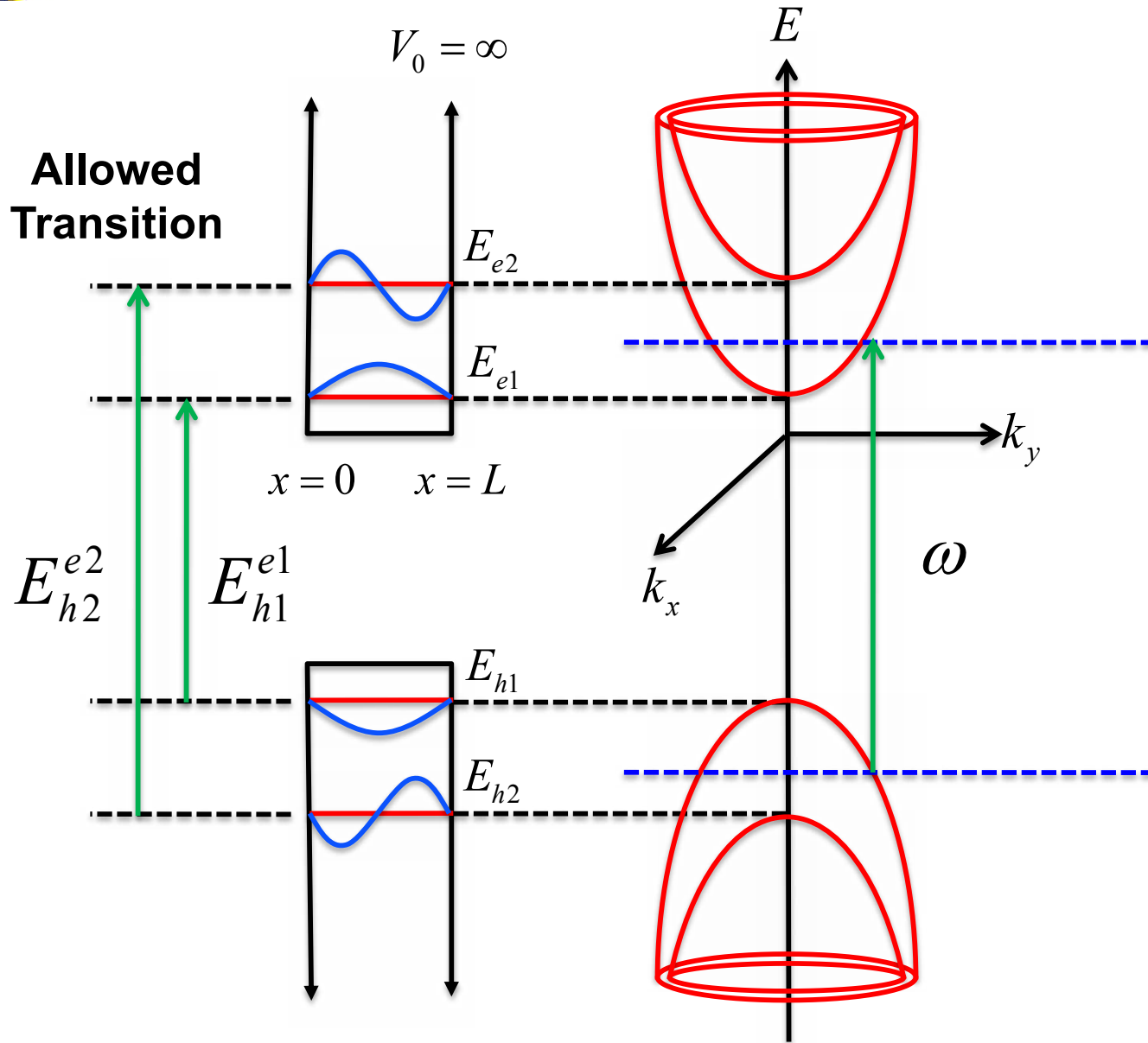
$$I_{hm}^{en} = \int_{-\infty}^{\infty} \phi_n^*(z) g_m(z) dz$$

Overlap integral of QW envelop wavefunctions

$$I_{hm}^{en} = \delta_{mn} \text{ for infinite potential well}$$



Interband Transitions in Quantum Wells (1)

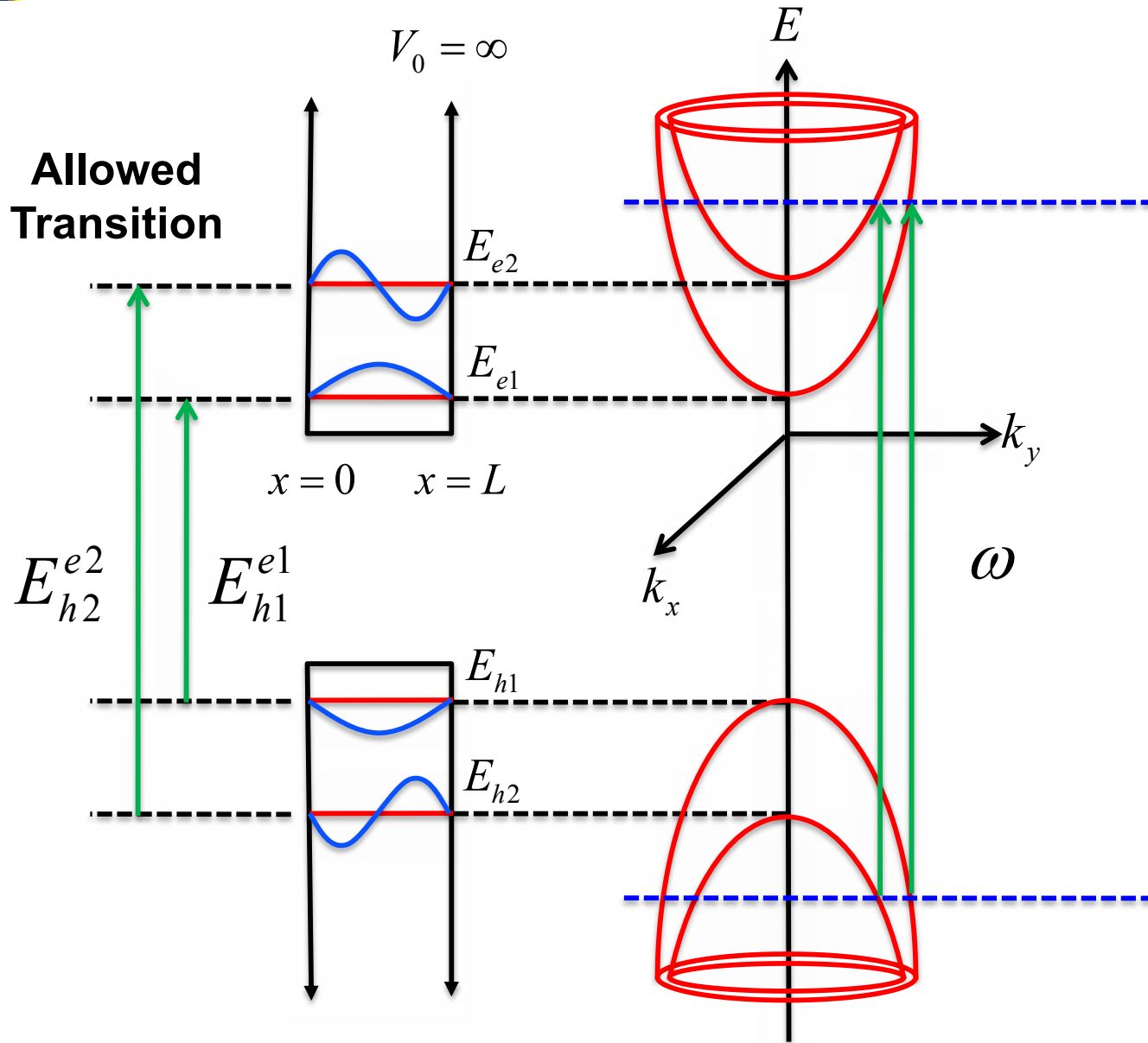


$$E_{h1}^{e1} < \omega < E_{h2}^{e2}$$

Only transition from $m=1$ hole subband to $n=1$ electron subband is allowed



Interband Transitions in Quantum Wells (2)



$$\hbar\omega > E_{h2}^{e2}$$

$$\begin{cases} m=1 \rightarrow n=1 \\ m=2 \rightarrow n=2 \end{cases}$$

Since the density of states for each subband is the same, the maximum optical gain is twice of that of a single-band transition



Optical Gain for Interband Transition in Quantum Wells

$$g(\hbar\omega) = C_0 \left| \hat{e} \cdot \vec{P}_{cv} \right|^2 \rho_r^{2d}(\hbar\omega) f_g(\hbar\omega)$$

$$\rho_r^{2d}(E) = \frac{m_r^*}{\pi \hbar^2 L_z} \sum_{n=1}^{\infty} H(E - E_{hn}^{en})$$

$$f_g(\hbar\omega) = f_C \left(E_{en} + \left(\hbar\omega - E_{hn}^{en} \right) \frac{m_r^*}{m_e^*} \right) - f_V \left(-E_{hm} - \left(\hbar\omega - E_{hn}^{en} \right) \frac{m_r^*}{m_h^*} \right)$$

For more general case:

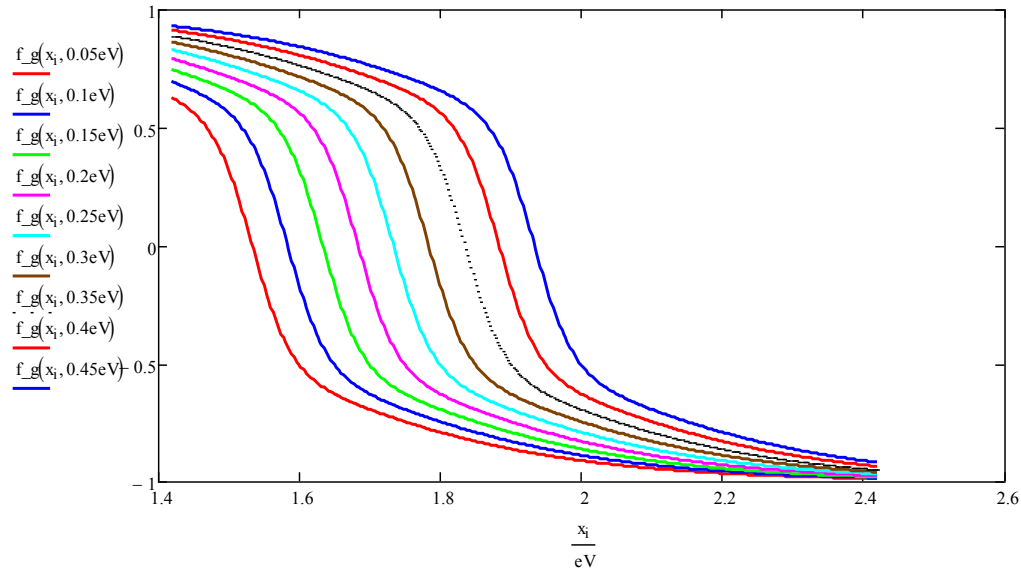
$$\Rightarrow g(\hbar\omega) = C_0 \left| \hat{e} \cdot \vec{P}_{cv} \right|^2 \sum_{m,n} \left| I_{hm}^{en} \right|^2 \rho_r^{2d} H(\hbar\omega - E_{hm}^{en}) f_g(\hbar\omega)$$

$$\rho_r^{2d} = \frac{m_r^*}{\pi \hbar^2 L_z}$$

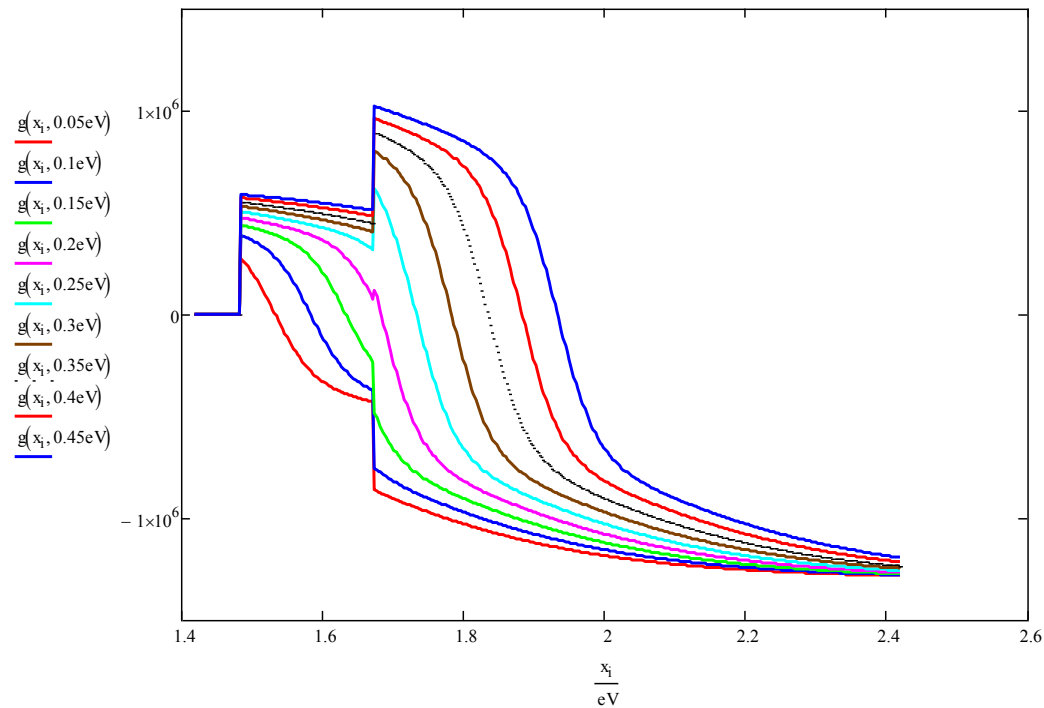


Quantum Well Gain

Fermi Inversion Factor



Gain





Solving Quasi-Fermi Level in Quantum Well

Electron concentration:

$$N = \int dE \rho_e^{2d}(E) f_C^n(E)$$

$$\rho_e^{2d}(E) = \frac{m_e^*}{\pi \hbar^2 L_z} \sum_{n=1}^{\infty} H(E - E_{en})$$

$$f_C^n(E) = \frac{1}{1 + e^{\frac{E_{en} + E_t - F_C}{k_B T}}}$$

Use $\int \frac{dx}{1 + e^x} = -\ln(1 + e^{-x})$

$$N = \sum_n \frac{m_e^* k_B T}{\pi \hbar^2 L_z} \ln \left(1 + e^{\frac{F_C - E_{en}}{k_B T}} \right)$$

For large quasi-Fermi Energy:

$$F_C \gg E_{en}$$

$$\ln \left(1 + e^{\frac{F_C - E_{en}}{k_B T}} \right) \approx \frac{F_C - E_{en}}{k_B T}$$

$$N = \sum_n \frac{m_e^*}{\pi \hbar^2 L_z} (F_C - E_{en})$$

For small quasi-Fermi Energy:

$$F_C \ll E_{en}$$

$$\ln \left(1 + e^{\frac{F_C - E_{en}}{k_B T}} \right) \approx e^{\frac{F_C - E_{en}}{k_B T}} = e^{\frac{E_{en} - F_C}{k_B T}}$$

$$N = \frac{m_e^* k_B T}{\pi \hbar^2 L_z} e^{\frac{E_{e1} - F_C}{k_B T}} = N_C e^{\frac{E_{e1} - F_C}{k_B T}}$$